

## N-Channel Enhancement Mode Field Effect Transistor

### General Description

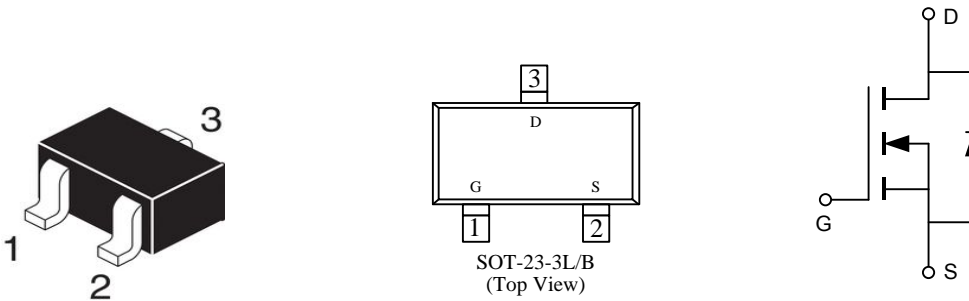
Product Summary		
$V_{DSS}$	$I_D$	$R_{DS(ON)}(m\Omega)TYP$
20V	3.6A	65 @ $V_{GS} = 4.5V$
		90 @ $V_{GS} = 2.5V$

### Features

- Super high dense cell design for low  $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23-3L/B package

### Package

- SOT-23-3L/B



### Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2302	-55°C to +150°C	SOT-23-3L/B	3000

### Absolute Maximum Ratings

( $T_A = 25^\circ C$  unless otherwise noted)

parameter	symbol	limit	unit
Drain-source voltage	$V_{DS}$	20	V
Gate-source voltage	$V_{GS}$	$\pm 8$	V
Drain current-continuous <sup>a</sup> @ $T_j = 125^\circ C$ -pulse $d^b$	$I_D$	3.6	A
	$I_{DM}$	12	A
Drain-source Diode forward current	$I_S$	1.25	A
Maximum power dissipation	$P_D$	1.25	W
Operating junction Temperature range	$T_j$	-55—150	$^\circ C$